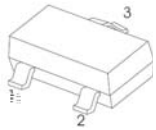
JCET

TRANSISTOR (NPN)

1. BASE
2.EMITTER
3.COLLECTOR



(T_a=25℃ unless otherwise noted)

	Collector-Base Voltage	75	V
	Collector-Emitter Voltage	40	V
	Emitter-Base Voltage	6	V
	Collector Current -Continuous	600	mA
	Collector Dissipation	300	mW
θ	Thermal Resistance, Junction to Ambient	417	℃/W
	Junction Temperature	50	℃
	Storage Temperature	-55~+150	℃

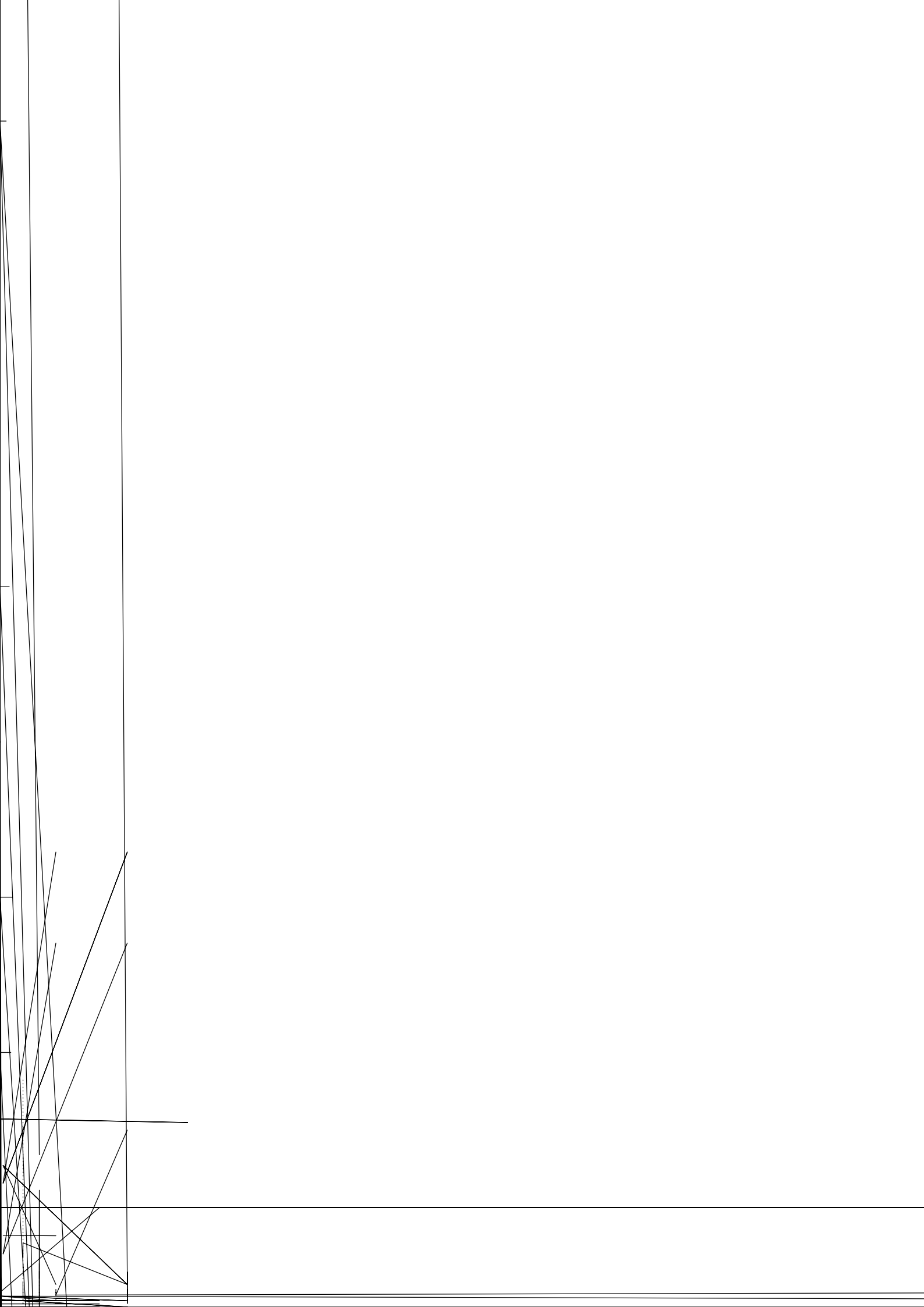
℃

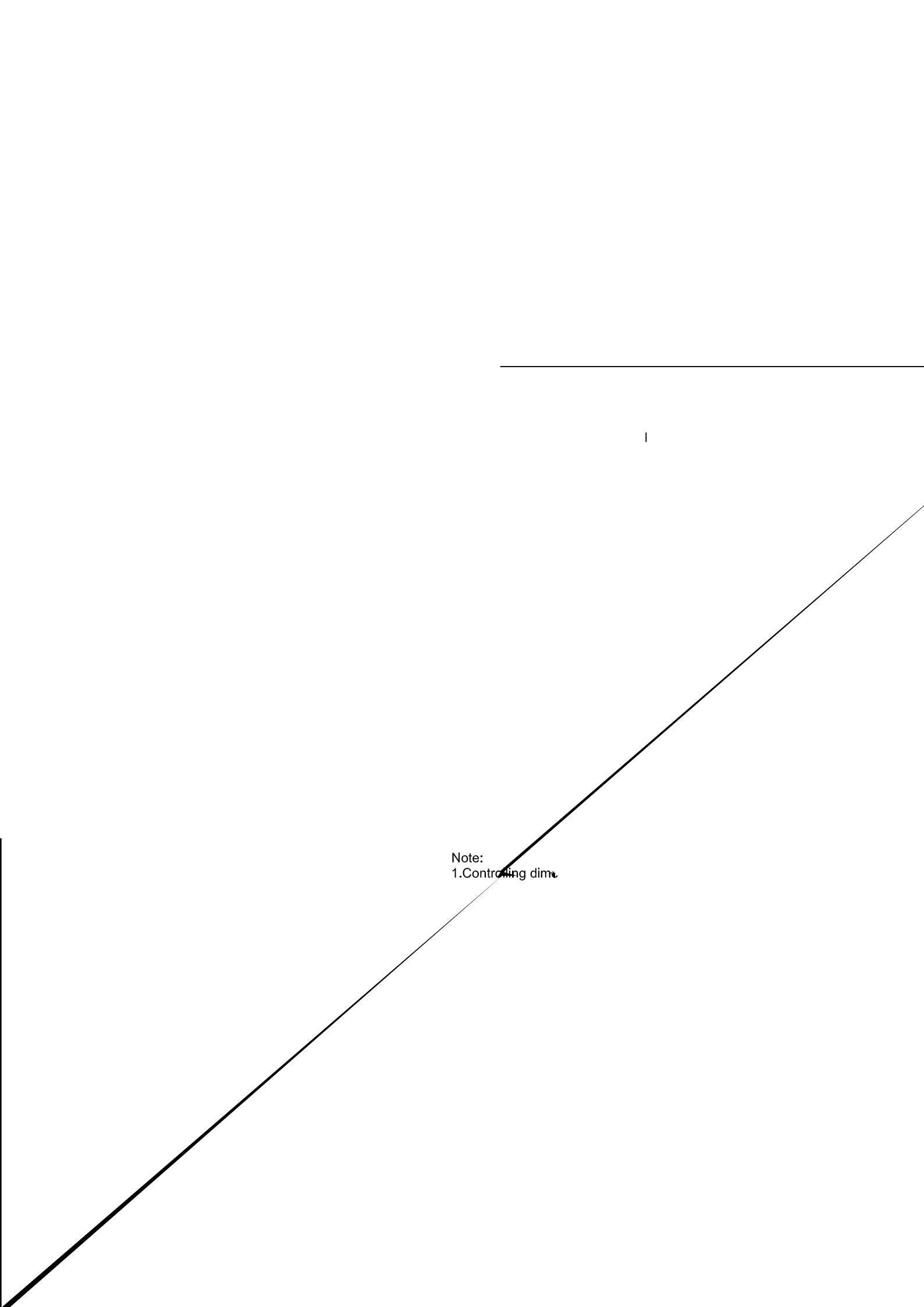
			in	yp	ax	Unit
	$V_{(BR)CBO}$	I_C= 10μA, I_E=0	75			V
	$V_{(BR)CEO}$*	I_C= 10mA, I_B=0	40			V
	$V_{(BR)EBO}$	I_E=10μA, I_C=0	6			V
	I_{CBO}	V_{CB}=60V, I_E=0			0.01	μA
	I_{CEX}	V_{CE}=30V,$V_{BE(off)}$=3V			0.01	μA
	I_{EBO}	V_{EB}= 3V, I_C=0			0.1	μA
	$h_{FE(1)}$*	V_{CE}=10V, I_C= 150mA	100		300	
	$h_{FE(2)}$	V_{CE}=10V, I_C= 0.1mA	40			
	$h_{FE(3)}$*	V_{CE}=10V, I_C= 500mA	42			
	$V_{CE(sat)}$*	I_C=500 mA, I_B= 50mA I_C=150 mA, I_B=15mA			1 0.3	V
	$V_{BE(sat)}$*	I_C=500 mA, I_B= 50mA I_C=150 mA, I_B=15mA			2.0 1.2	V
	f_T	V_{CE}=20V, I_C= 20mA, f=100MHz	300			MHz
	t_d	V_{CC}=30V, $V_{BE(off)}$=-0.5V I_C=150mA , I_{B1}= 15mA			10	ns
	t_r				25	ns
	t_S	V_{CC}=30V, I_C=150mA I_{B1}=-I_{B2}=15mA			225	ns
	t_f				60	ns

*pulse test: Pulse Width ≤300μs, Duty Cycle≤ 2.0%.

CLASSIFICATION OF $h_{FE(1)}$

RANK	L	H
RANGE	100 200	200 300
MARKING	1P	





Note:
1.Controlling dim


2000
1
1000
900